



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

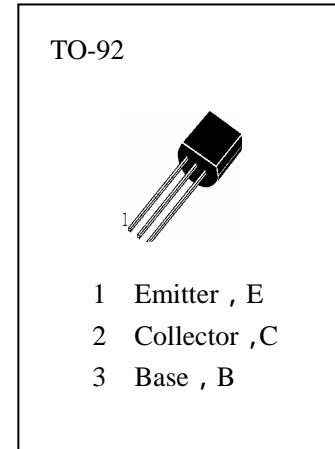
H3279

STROBE FLASH APPLICATIONS

MEDIUM POWER AMPLIFIER APPLICATIONS

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature..... -55~150
 T_j —Junction Temperature..... 150
 P_c —Collector Dissipation..... 750mW
 V_{CBO} —Collector-Base Voltage..... 30V
 V_{CEO} —Collector-Emitter Voltage..... 10V
 V_{EBO} —Emitter-Base Voltage..... 6V
 I_c —Collector Current..... 2A
 I_{CP} —Collector Current (Pulse) 5A



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	30			V	$I_C=100 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	10			V	$I_C=10mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	6			V	$I_E=1mA, I_C=0$
$HFE(1)$	DC Current Gain	140		600		$V_{CE}=-1V, I_C=-500mA$
$HFE(2)$		70				$V_{CE}=1V, I_C=2A$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.5	V	$I_C=2A, I_B=50mA$
V_{BE}	Base-Emitter Voltage			1.5	V	$V_{CE}=1V, I_C=2A$
I_{CBO}	Collector Cut-off Current			100	nA	$V_{CB}=30V, I_E=0$
I_{CEO}	Collector Cut-off Current			100	nA	$V_{CE}=10V, I_B=0$
I_{EBO}	Emitter Cut-off Current			100	nA	$V_{EB}=6V, I_C=0$
f_T	Current Gain-Bandwidth Product		150		MHz	$V_{CE}=1V, I_C=0.5A$
C_{ob}	Output Capacitance			27	pF	$V_{CB}=10V, I_E=0, f=1MHz$

hfe Classification

Y

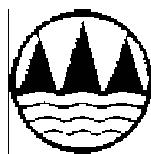
GR

BL

140—280

200—400

300—600



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